

AMENDMENTS TO THE ABSTRACT

Please replace the abstract with the following amended abstract:

Disclosed is a method of manufacturing a semiconductor device. A floating gate is formed and a nitrification process is then implemented. With the disclosed process, It is thus possible to improve the roughness of the top surface of the floating gate electrode. Furthermore, a nitrification process and a dielectric film formation process are implemented in-situ.~~—It is possible to simplify which simplifies the manufacturing process.~~